

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China











NPN PRE-BIASED SMALL SIGNAL SURFACE MOUNT TRANSISTOR

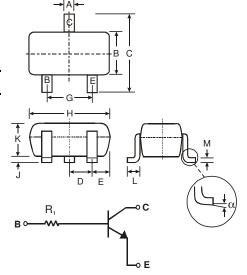
Features

- Epitaxial Planar Die Construction
- Complementary PNP Types Available (DDTA)
- Built-In Biasing Resistor, R1 only
- Lead Free/RoHS Compliant (Note 2)
- "Green" Device (Note 3 and 4)

Mechanical Data

- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound, Note 4. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Marking Information: See Diagrams & Page 3
- Type Code: See Table Below Ordering Information: See Page 3 Weight: 0.006 grams (approximate)

P/N	R1 (NOM)	Type Code
DDTC113TUA	1ΚΩ	N01
DDTC123TUA	2.2ΚΩ	N03
DDTC143TUA	4.7ΚΩ	N07
DDTC114TUA	10ΚΩ	N12
DDTC124TUA	22ΚΩ	N16
DDTC144TUA	47ΚΩ	N19
DDTC115TUA	100KΩ	N23
DDTC125TUA	200ΚΩ	N25



	SOT-323							
Dim	Min	Max						
Α	0.25	0.40						
В	1.15	1.35						
С	2.00 2.20							
D	0.65 N	ominal						
E	0.30	0.40						
G	1.20	1.40						
Н	1.80	2.20						
J	0.0	0.10						
K	0.90	1.00						
L	0.25	0.40						
М	0.10	0.18						
α	0°	8°						
All Dimensions in mm								

SCHEMATIC DIAGRAM

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit	
Collector-Base Voltage	V _{CBO}	50	V	
Collector-Emitter Voltage	V _{CEO}	50	V	
Emitter-Base Voltage	V _{EBO}	5	V	
Collector Current	I _C (Max)	100	mA	
Power Dissipation	P _d	200	mW	
Thermal Resistance, Junction to Ambient Air (Note 1)	$R_{ hetaJA}$	833	°C/W	
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C	

Notes:

- Mounted on FR4 PC Board with recommended pad layout as shown on Diodes Inc., suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf
- No purposefully added lead.
- Diodes Inc.'s "Green" Policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- Product manufactured with date code 0627 (week 27, 2006) and newer are built with Green Molding Compound. Product manufactured prior to date code 0627 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants

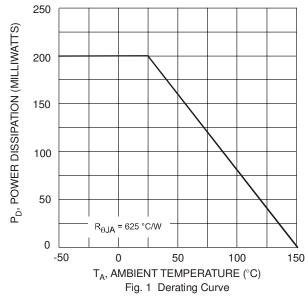


Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	50	_	_	V	$I_C = 50\mu A$
Collector-Emitter Breakdown Voltage	BV _{CEO}	50	_	_	٧	$I_C = 1mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	5	_	_	٧	$I_E = 50\mu A$
Collector Cutoff Current	I _{CBO}	_	_	0.5	μΑ	$V_{CB} = 50V$
Emitter Cutoff Current	I _{EBO}		_	0.5	μΑ	$V_{EB} = 4V$
Collector-Emitter Saturation Voltage	VCE(sat)	-	_	0.3	V	$\begin{split} I_{C/IB} &= 10 \text{mA/1mA} & \text{DDTC113TUA} \\ I_{C/IB} &= 5 \text{mA/0.5mA} & \text{DDTC123TUA} \\ I_{C/IB} &= 2.5 \text{mA/.25mA} & \text{DDTC143TUA} \\ I_{C/IB} &= 1 \text{mA/.1mA} & \text{DDTC114TUA} \\ I_{C/IB} &= 5 \text{mA/0.5mA} & \text{DDTC124TUA} \\ I_{C/IB} &= 2.5 \text{mA/.25mA} & \text{DDTC144TUA} \\ I_{C/IB} &= 1 \text{mA/0.1mA} & \text{DDTC115TUA} \\ I_{C/IB} &= .5 \text{mA/.05mA} & \text{DDTC125TUA} \\ \end{split}$
DC Current Transfer Ratio	h_FE	100	250	600		$I_C = 1 \text{mA}, V_{CE} = 5 \text{V}$
Input Resistor (R ₁) Tolerance	ΔR_1	-30	_	+30	%	_
Gain-Bandwidth Product*	f _T		250		MHz	$V_{CE} = 10V, I_{E} = -5mA,$ f = 100MHz

^{*}Transistor - For Reference Only

Typical Curves - DDTC114TUA



75°C

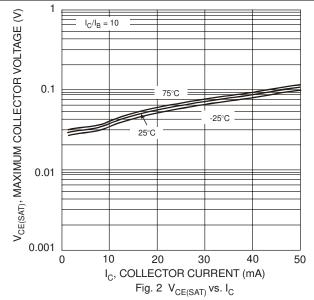


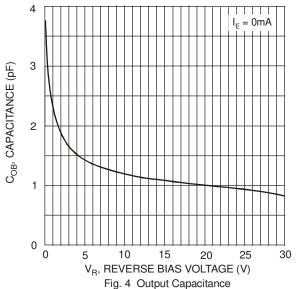
V_{CE} = 10

25°C

10

I_C, COLLECTOR CURRENT (mA) Fig. 3 DC Current Gain





1,000

100

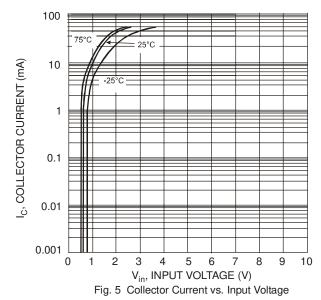
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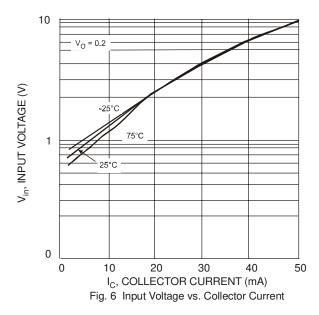
1

h_{FE}, DC CURRENT GAIN (NORMALIZED)

100





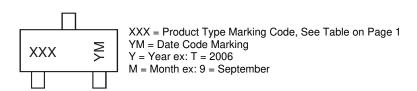


Ordering Information (Note 4 & 5)

Device	Packaging	Shipping			
DDTC1xxTUA-7-F	SOT-323	3000/Tape & Reel			
DDTC1xxTUA-13-F	SOT-323	10,000/Tape & Reel			

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



Date Code Key

Year	200	2006 2007			2008	008 2009		2010		2011	2	2012	
Code	Т		U		V	V	٧	Χ		Υ		Z	
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec	
Code	1	2	3	4	5	6	7	8	9	0	N	D	

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